

C3D20065A SiC Schottky Barrier Diode

V	650V
I _e	20A
Q _c	47nC

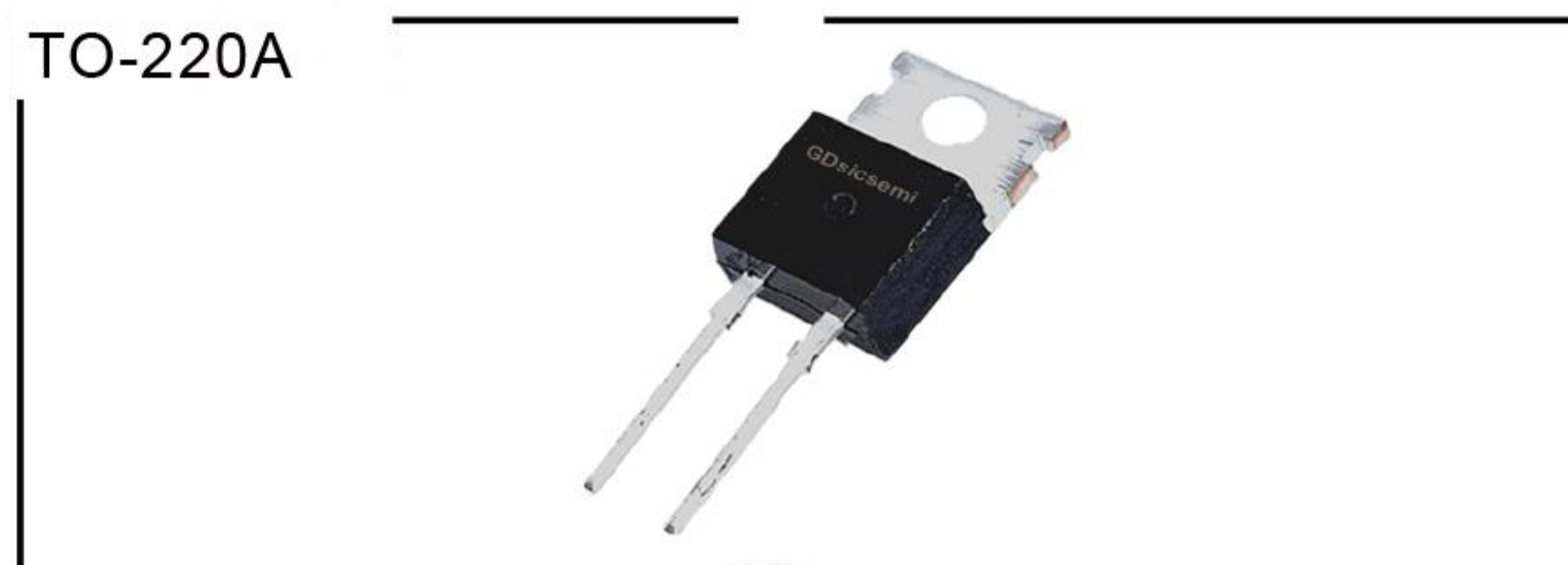
· Features

- 1) Shorter recovery time
- 2) Reduced temperature dependence
- 3) High-speed switching possible
- 4) High surge current capability

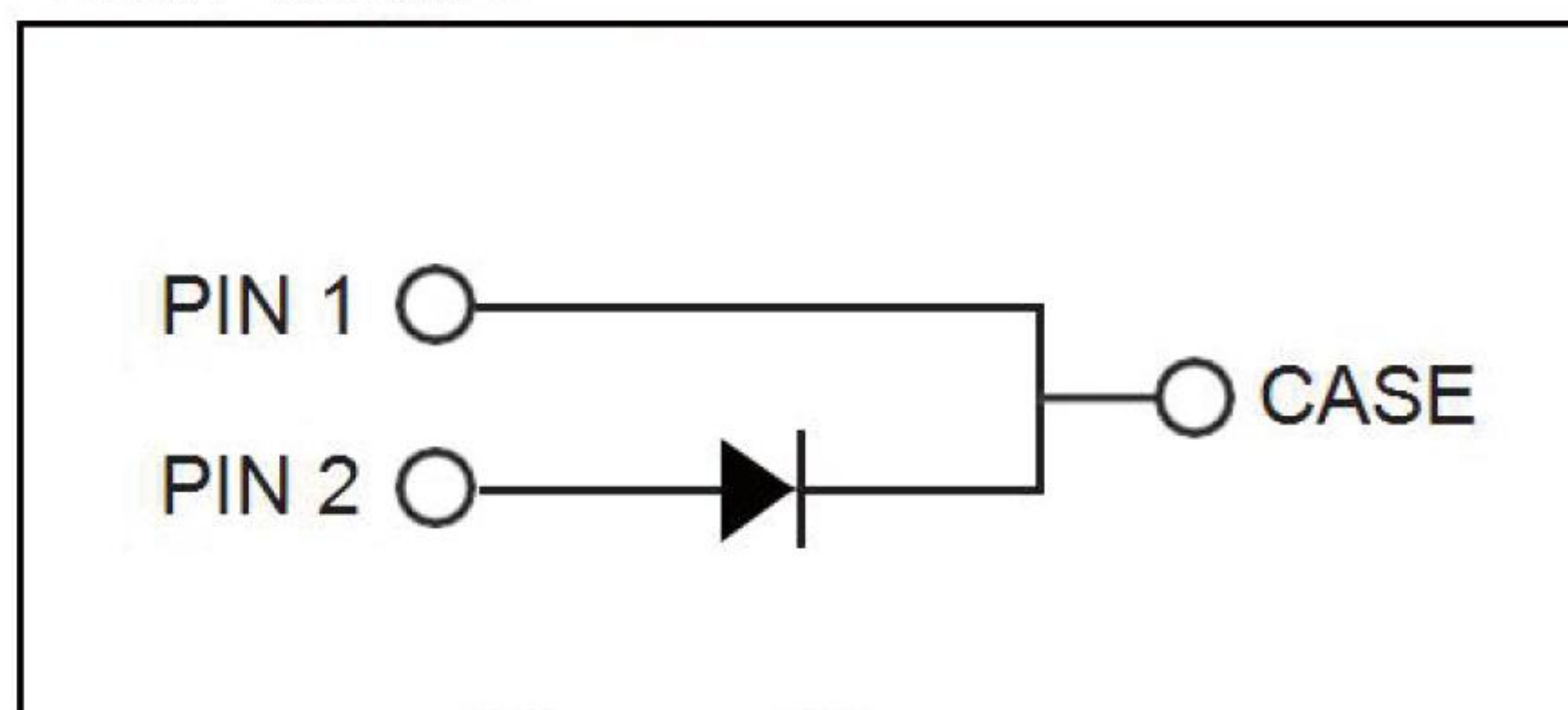
· Construction

Silicon carbide epitaxial planar type

· Outline TO-220A



· Inner Circuit



· Packaging Specifications

	Packaging	Tube
Type	Reel size (mm)	-
	Tape width (mm)	-
	Basic ordering unit (pcs)	50
	Packing code	C9
	Marking	C3D20065A

● Absolute Maximum Ratings (T_j = 25°C)

Parameter	Symbol	Value	Unit	
Reverse voltage (repetitive peak)	V _{RM}	650	V	
Reverse voltage (DC)	V _R	650	V	
Continuous forward current (T _c =125°C)	I _F	20	A	
Surge non-repetitive forward current	I _{FSM}	PW=10ms sinusoidal, T _j =25°C	123	A
		PW=10ms sinusoidal, T _j =150°C	104	A
		PW=10μs square, T _j =25°C	450	A
Repetitive peak forward current	I _{FRM}	81 ^{*1}	A	
i ² t value	∫ i ² dt	1 ≤ PW ≤ 10ms, T _j =25°C	75	A ² s
		1 ≤ PW ≤ 10ms, T _j =150°C	54	A ² s
Total power dissipation	P _D	115 ^{*2}	W	
Junction temperature	T _j	175	°C	
Range of storage temperature	T _{stg}	-55 to +175	°C	

*1 T_c=100°C, T_j=150°C, Duty cycle=10% *2 T_c=25°C

●Electrical characteristics ($T_j = 25^\circ\text{C}$)

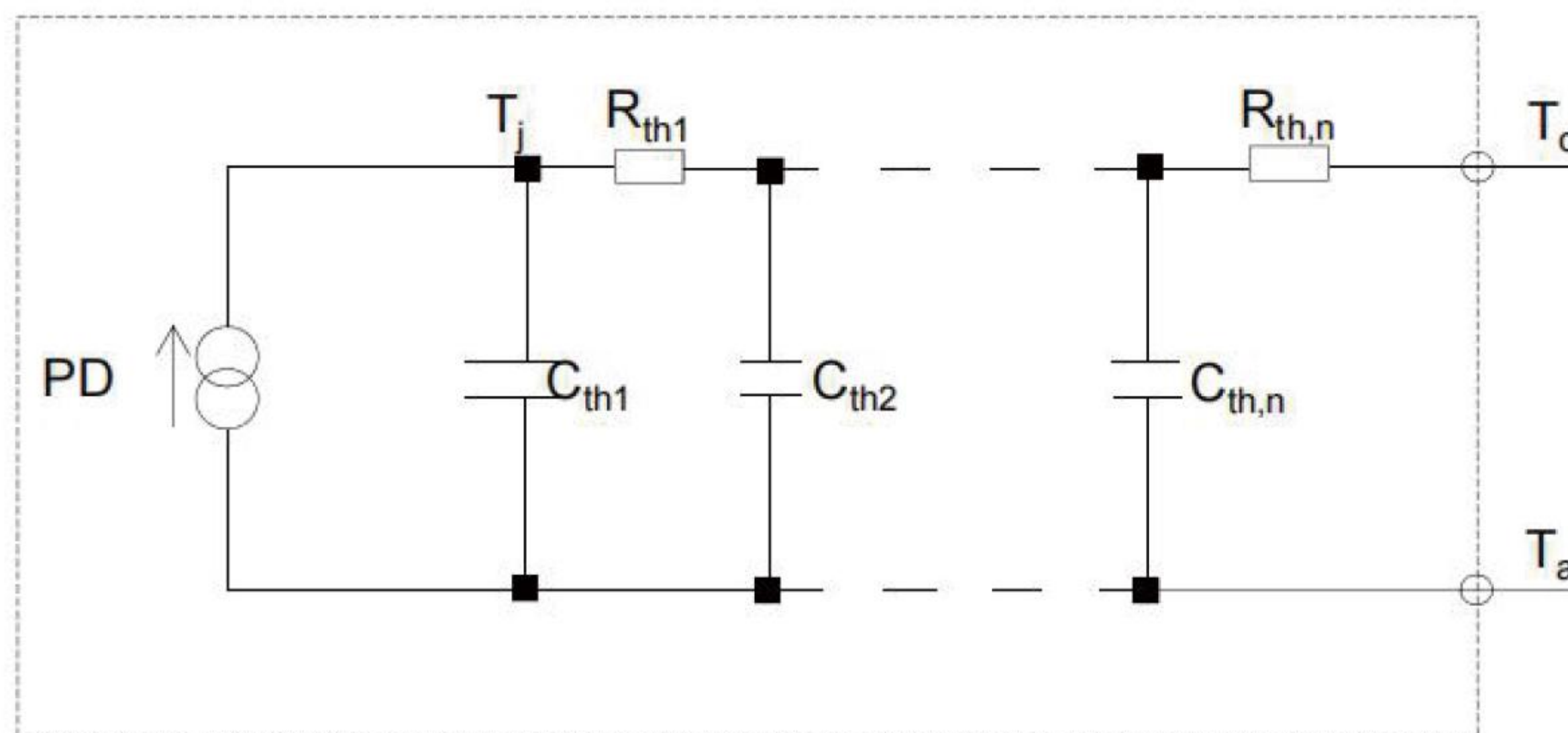
Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
DC blocking voltage	V_{DC}	$I_R=100\mu\text{A}$	650	-	-	V
Forward voltage	V_F	$I_F=20\text{A}, T_j=25^\circ\text{C}$	-	1.35	1.50	V
		$I_F=20\text{A}, T_j=150^\circ\text{C}$	-	1.44	1.71	V
		$I_F=20\text{A}, T_j=175^\circ\text{C}$	-	1.50	-	V
Reverse current	I_R	$V_R=650\text{V}, T_j=25^\circ\text{C}$	-	0.06	100	μA
		$V_R=650\text{V}, T_j=150^\circ\text{C}$	-	4	400	μA
		$V_R=650\text{V}, T_j=175^\circ\text{C}$	-	12	-	μA
Total capacitance	C	$V_R=1\text{V}, f=1\text{MHz}$	-	1000	-	pF
		$V_R=650\text{V}, f=1\text{MHz}$	-	91	-	pF
Total capacitive charge	Q_C	$V_R=400\text{V}, di/dt=350\text{A}/\mu\text{s}$	-	47	-	nC
Switching time	t_C	$V_R=400\text{V}, di/dt=350\text{A}/\mu\text{s}$	-	25	-	ns
Non-repetitive Avaranche Energy	E_{ava}	$L=1\text{mH}$	-	220	-	mJ

●Thermal characteristics

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance	$R_{th(j-c)}$	-	-	0.87	1.3	$^\circ\text{C}/\text{W}$

●Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
R_{th1}	8.13E-04	K/W	C_{th1}	9.17E-05	Ws/K
R_{th2}	4.07E-02		C_{th2}	5.94E-04	
R_{th3}	8.31E-01		C_{th3}	1.68E-03	



●Electrical characteristic curves

Fig.1 $V_F - I_F$ Characteristics

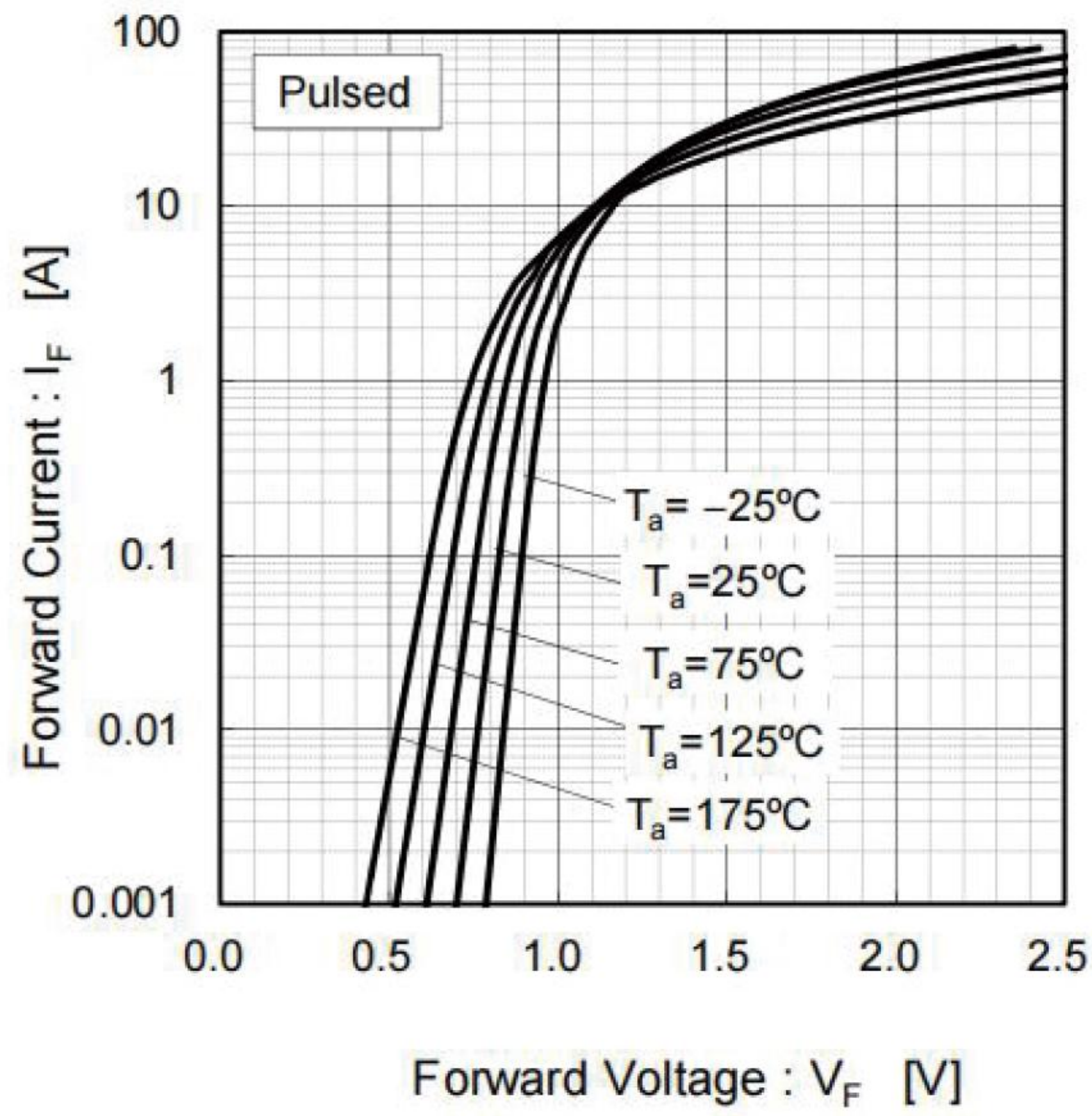


Fig.2 $V_F - I_F$ Characteristics

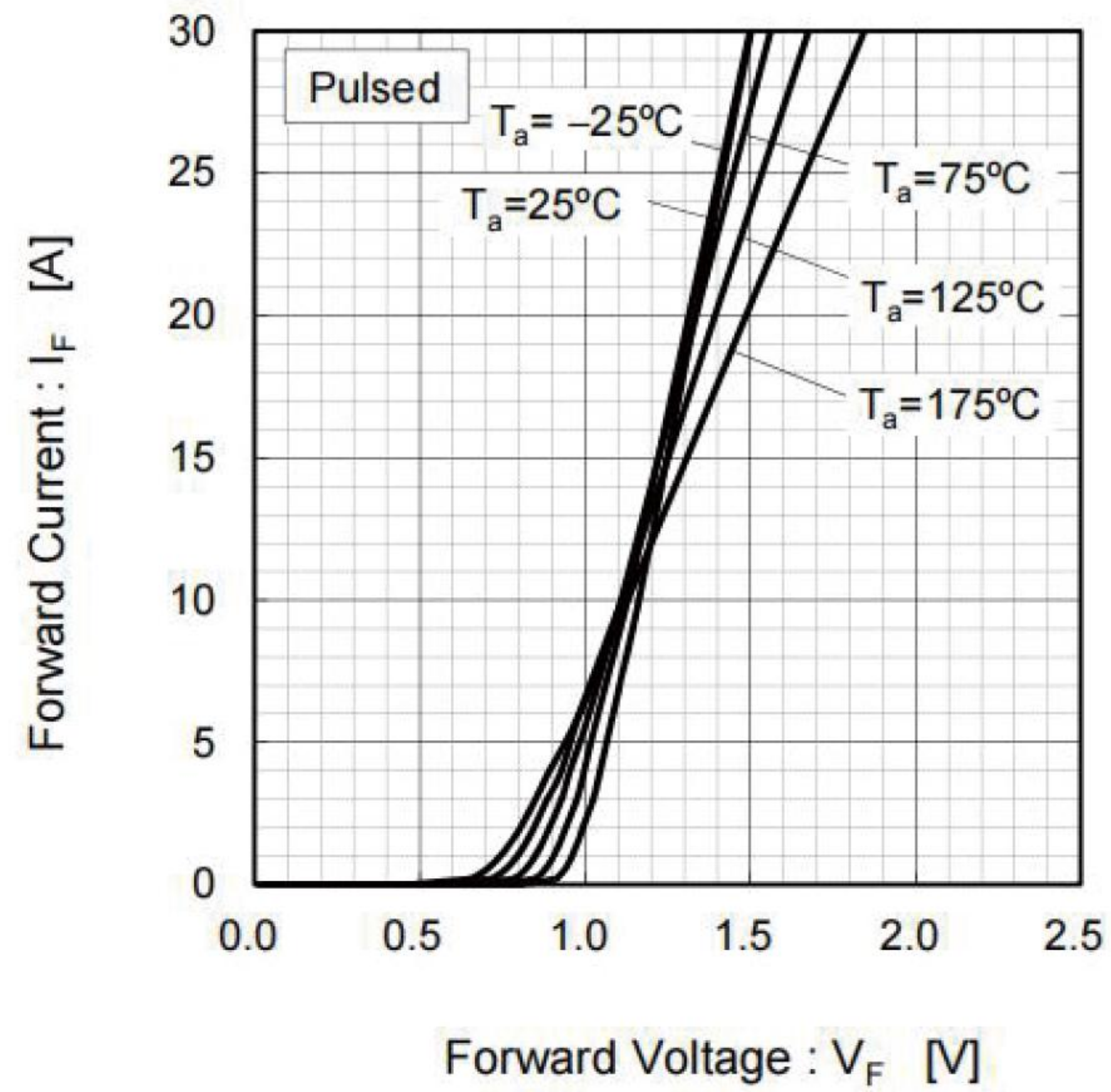


Fig.3 $V_R - I_R$ Characteristics

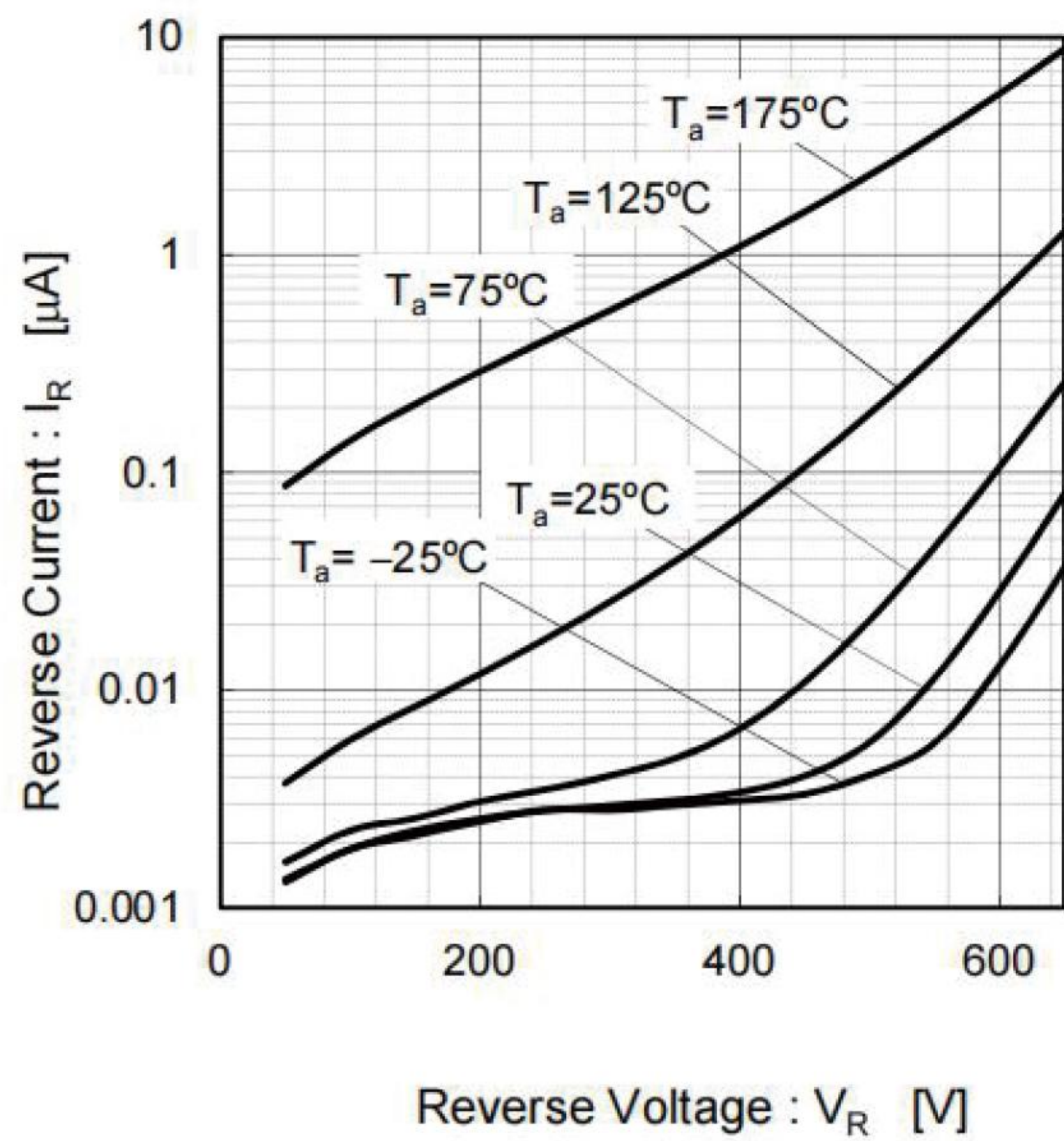
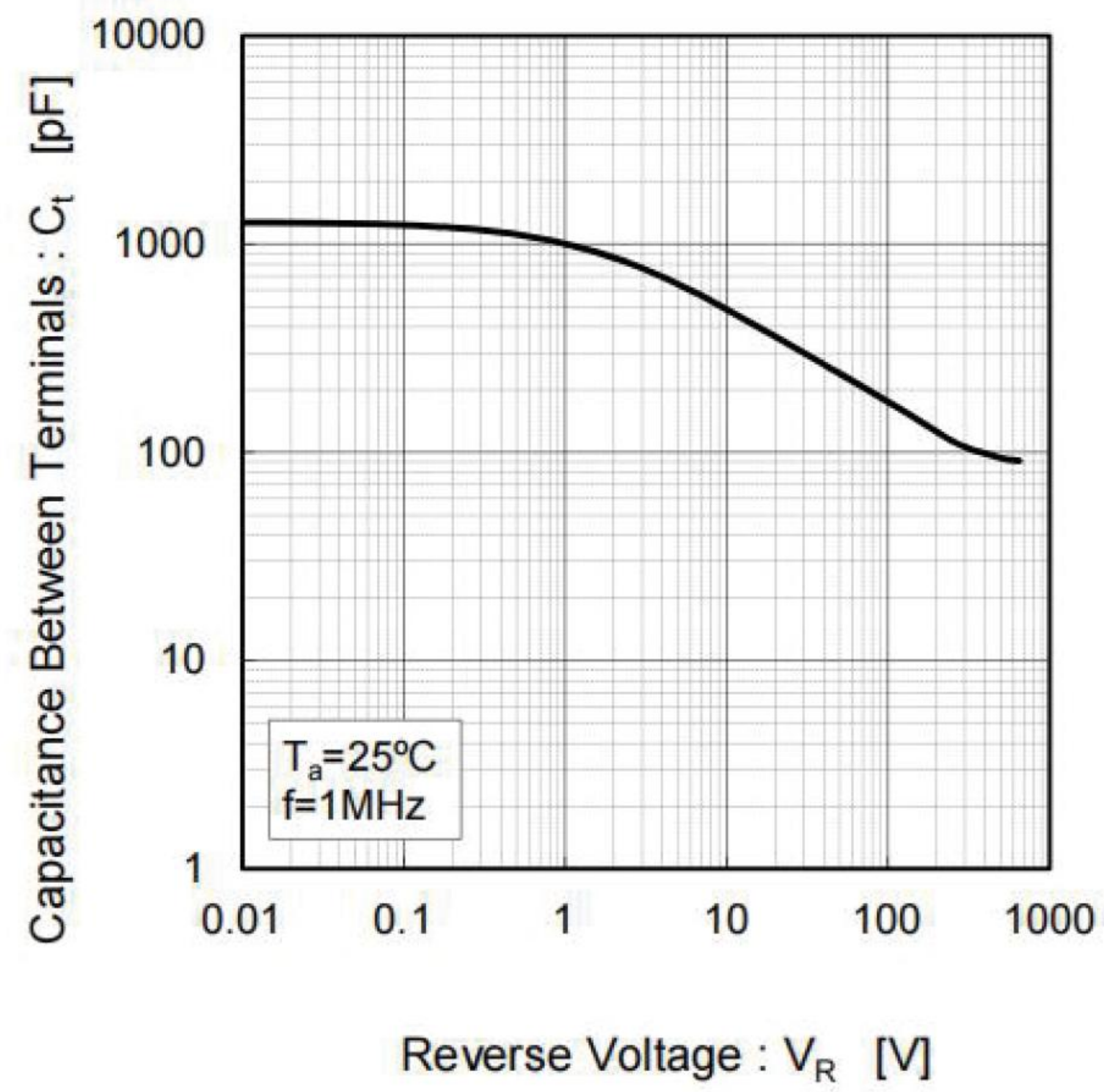


Fig.4 $V_R - C_t$ Characteristics



●Electrical characteristic curves

Fig.5 Typical Transient Thermal Resistance vs. Pulse Width

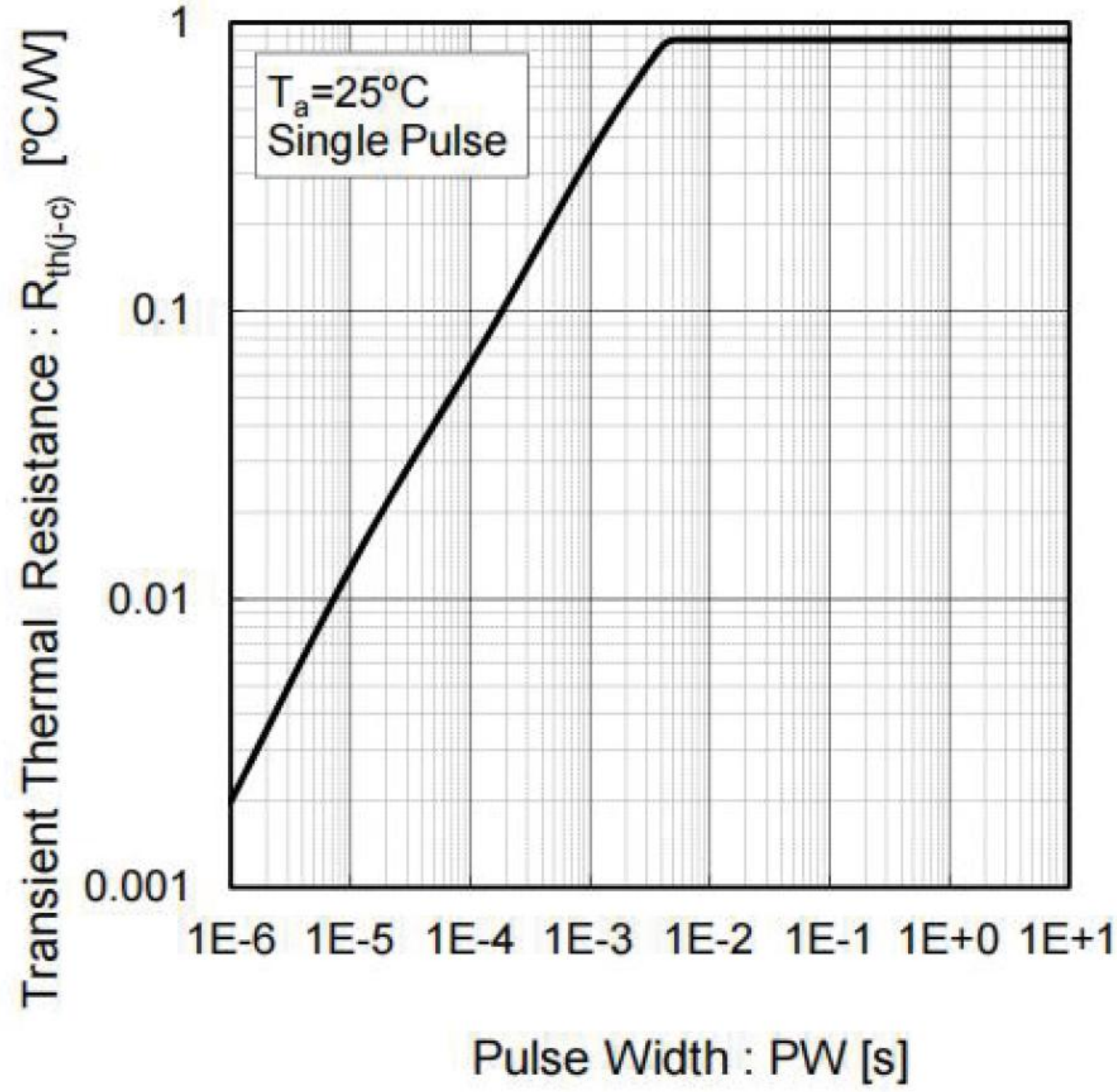


Fig.6 Power Dissipation

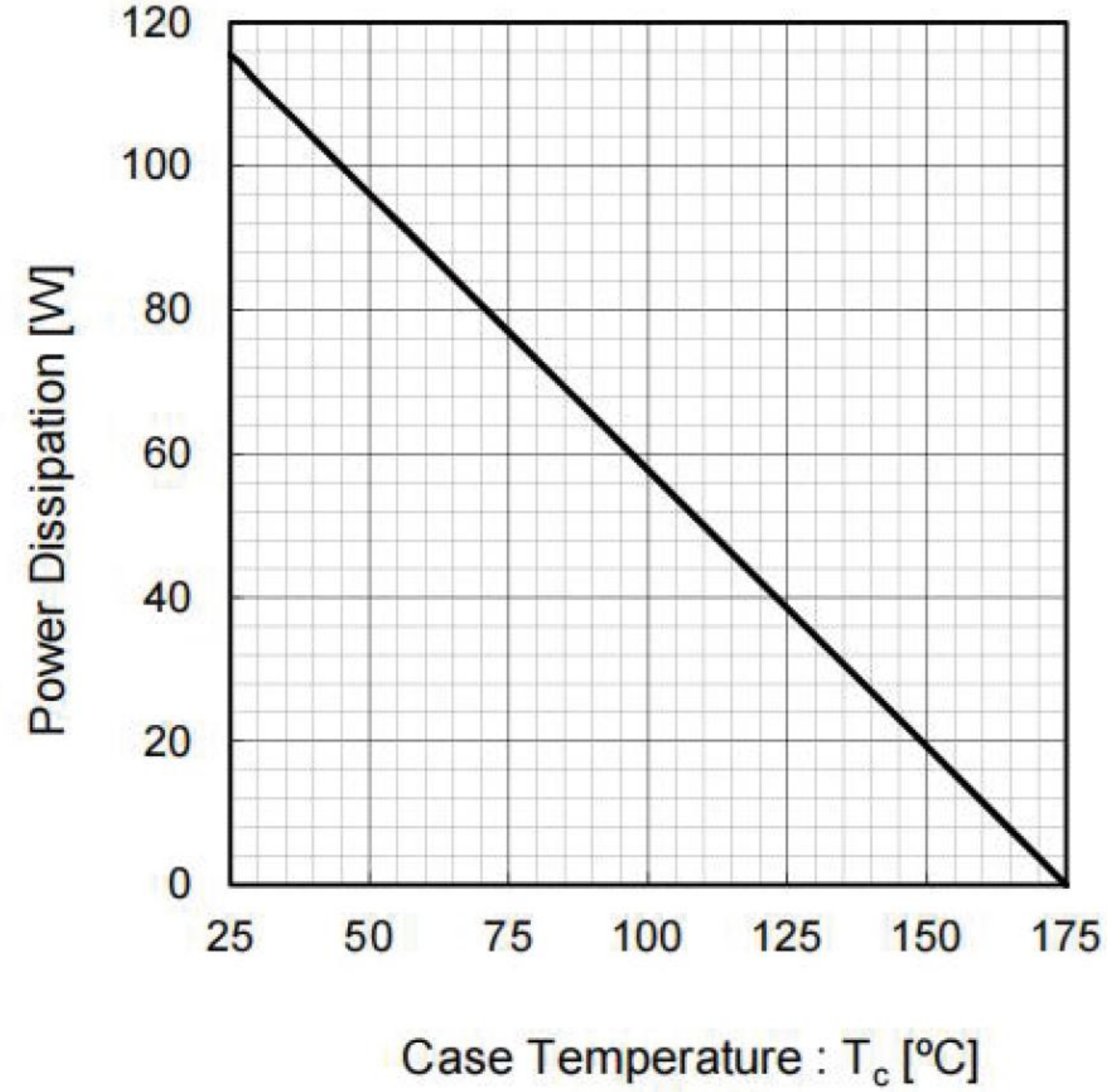
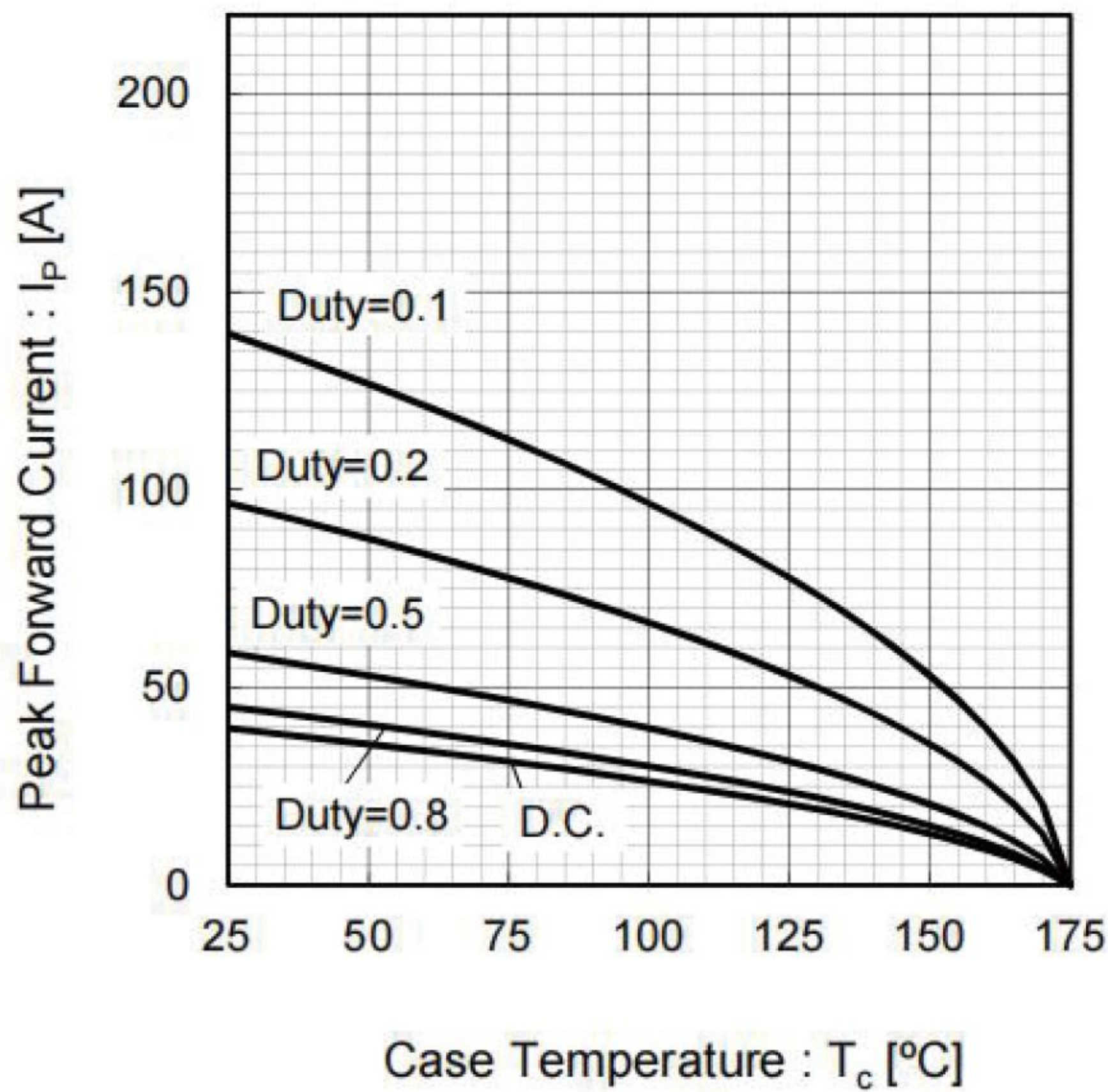
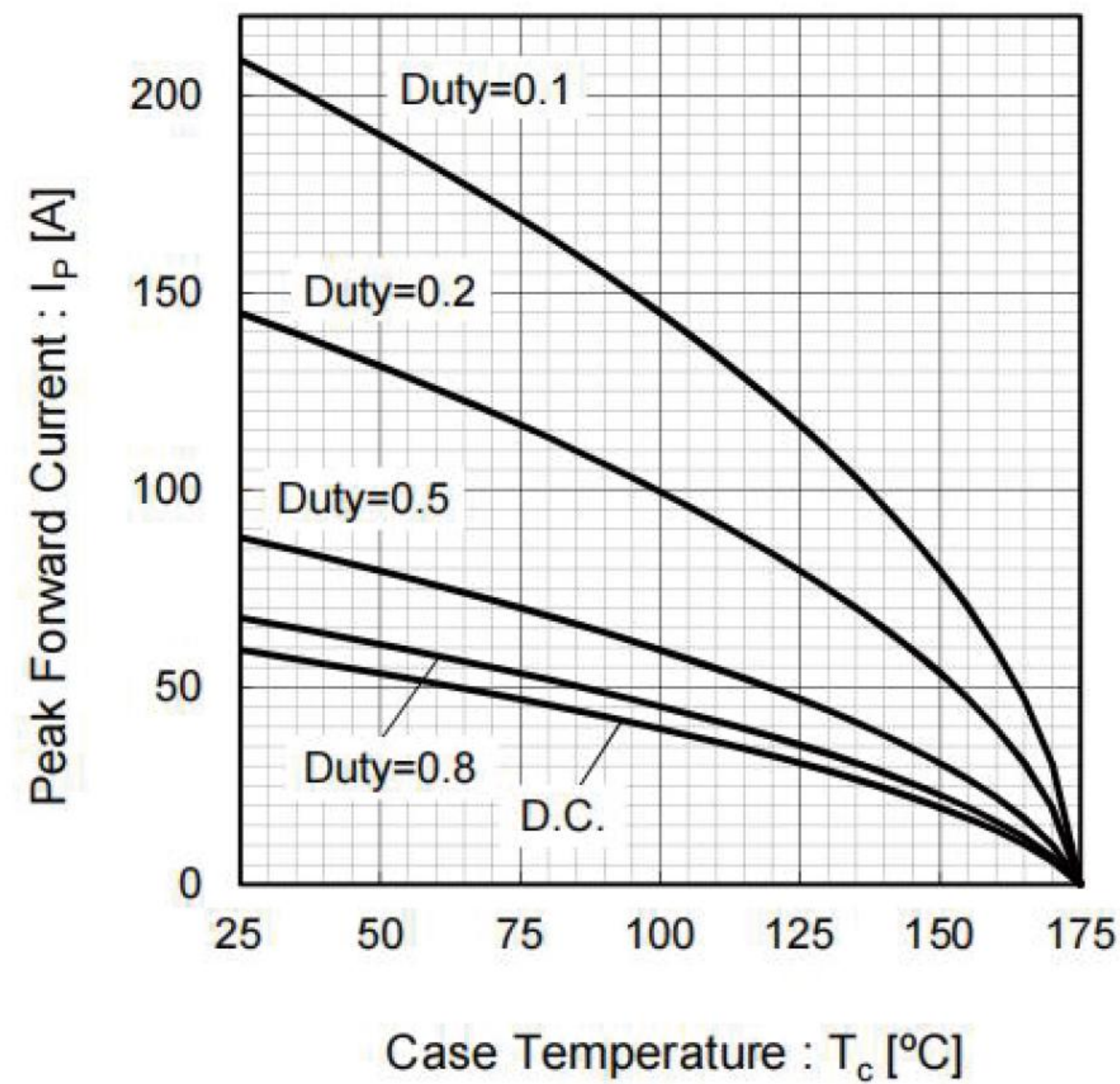


Fig.7*3 Maximum peak forward current derating curve $I_P - T_c$



*3 Based on max V_f , max $R_{th(j-c)}$
Valid for switching of above 10kHz,
excluding D.C. curve.

Fig.8*4 Typical peak forward current derating curve $I_P - T_c$ (Not guaranteed)



*4 Based on typ V_f , typ $R_{th(j-c)}$
Typical value, not guaranteed
Valid for switching of above 10kHz,
excluding D.C. curve

●Electrical characteristic curves

Fig.9 Surge non-repetitive forward current vs. Pulse width (Sinusoidal waveform)

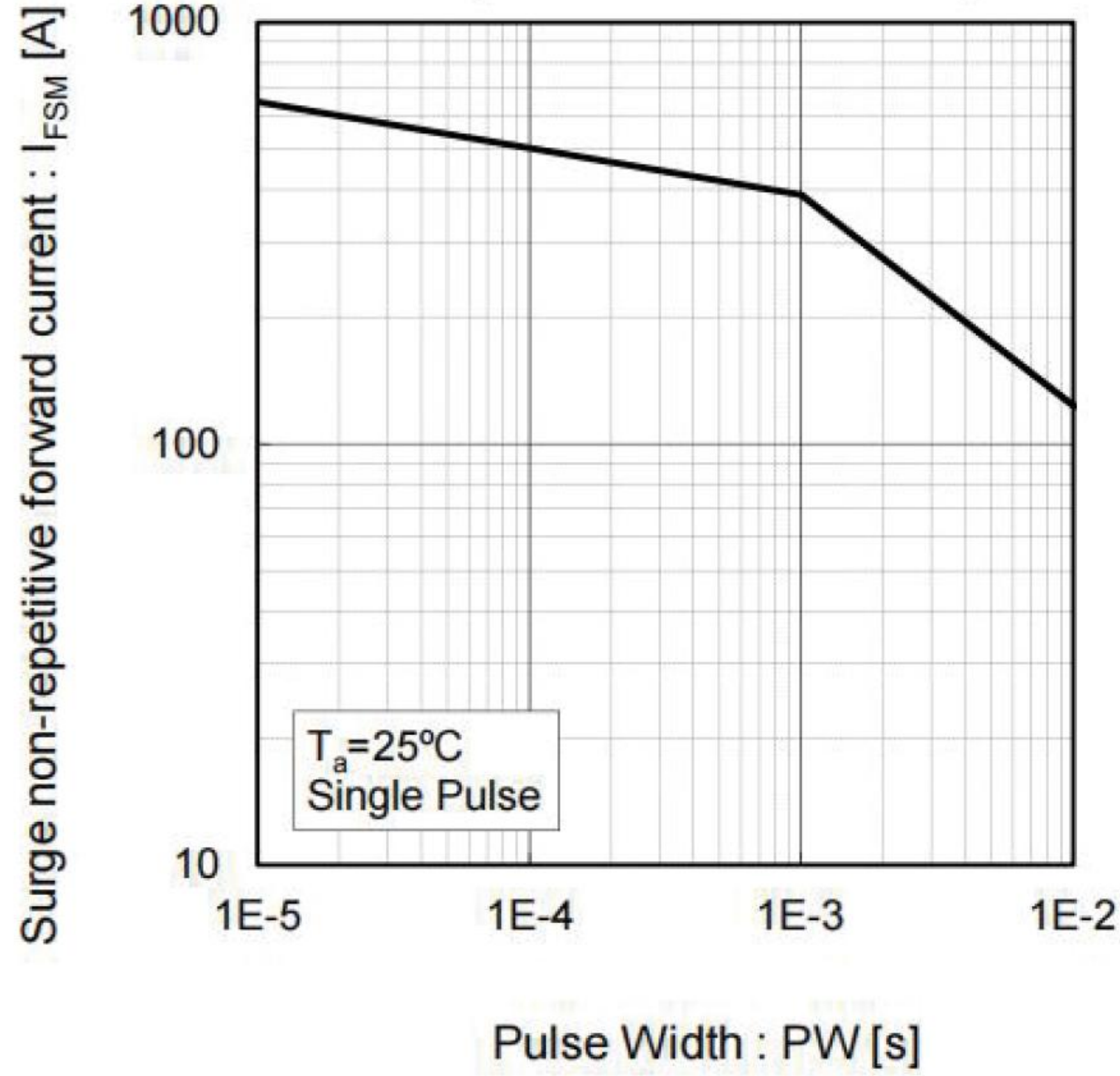


Fig.10 Typical capacitance store energy

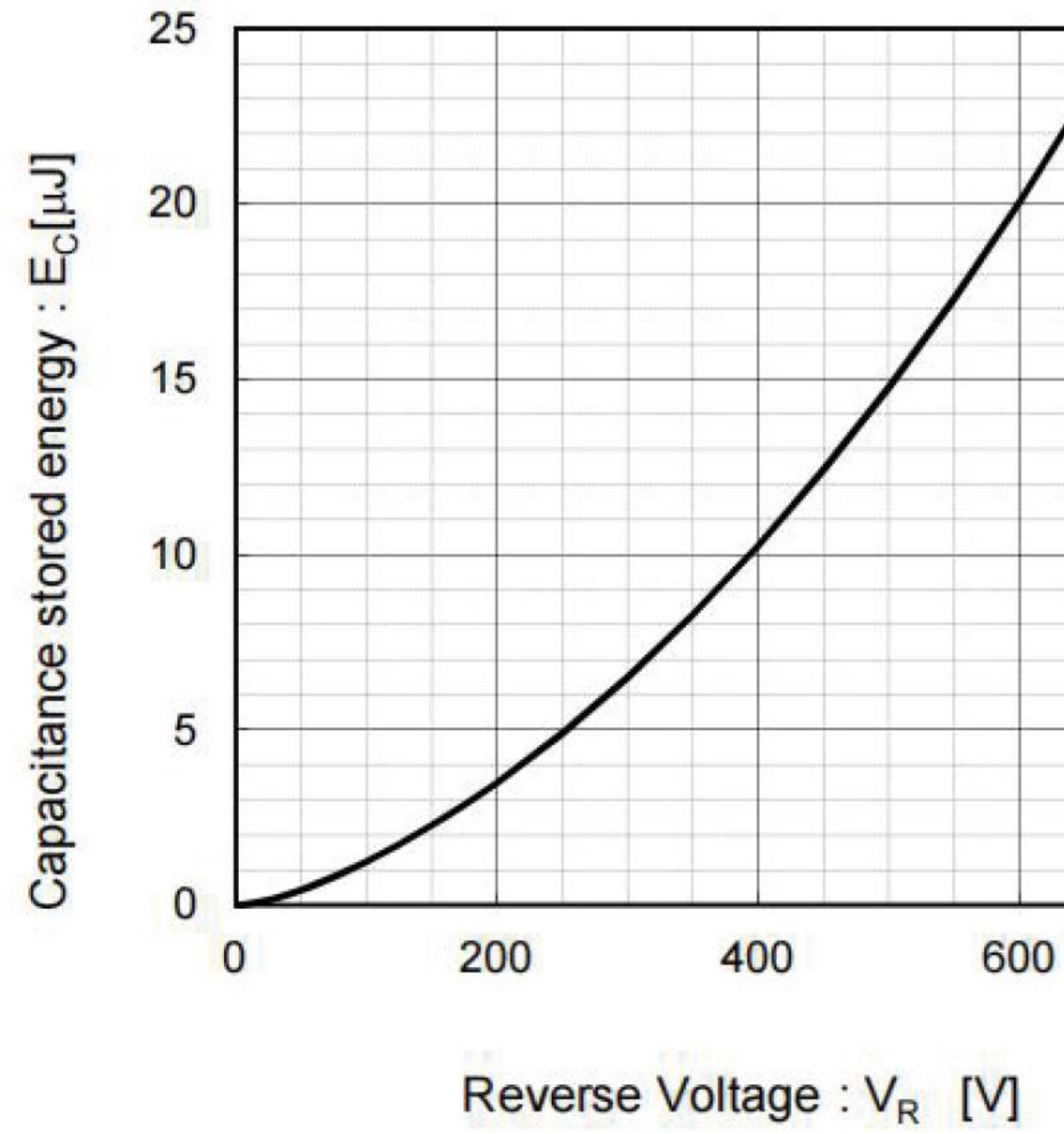
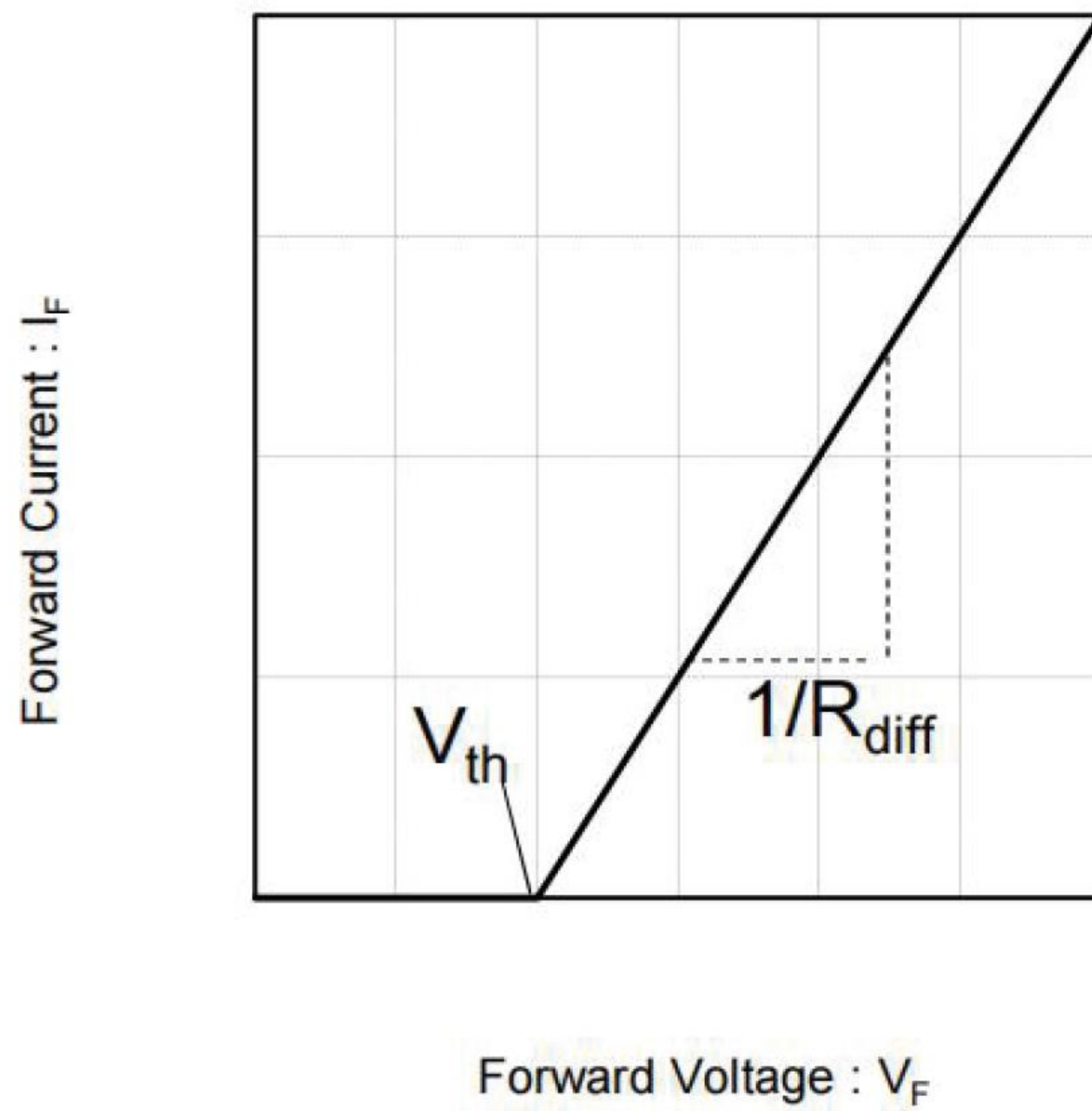


Fig.11 Equivalent forward current curve



$$V_F = V_{th} + R_{diff} I_F$$

$$V_{th}(T_j) = a_0 + a_1 T_j$$

$$R_{diff}(T_j) = b_0 + b_1 T_j + b_2 T_j^2$$

Symbol	Typical Value	Unit
a_0	9.66E-01	V
a_1	-1.10E-03	V/°C
b_0	1.76E-02	Ω
b_1	3.73E-05	Ω/°C
b_2	3.84E-07	Ω/°C ²

T_j in °C; -55 °C < T_j < 175°C ; I_F < 40A